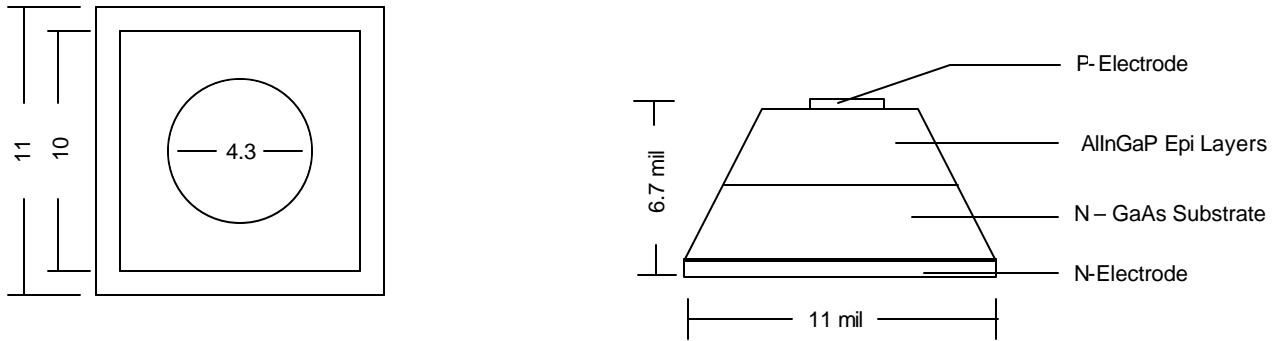


TCE11UGU



- ❖ Features:
 - AlInGaP/GaAs LED Chips
 - High luminous intensity
 - Low driving current
 - Indoor/Outdoor applications
 - 100% probing test

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	11 mil x 11 mil	280 μm x 280 μm
		Thickness	6.7 mil	170 μm
		Emission area	10 mil	254 μm
		Bonding pad	4.3 mil	110 μm
Electrode	Top	P (anode)	Gold alloy	
	Backside	N (cathode)	Gold alloy	

GREEN

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Forward Voltage	V_F	$I_F = 10\mu\text{A}$	1.50	-	-	V	
		$I_F = 20\text{mA}$	-	-	2.40		
Wavelength	λ_p	$I_F = 20\text{mA}$	-	562	-	nm	
	λ_d		557	561	565		
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	20	-	nm	
Reverse Voltage	I_R	$V_R = 10\text{V}$	-	-	100	μA	
Luminous Intensity	I_v	$I_F = 20\text{mA}$	E2	6	-	-	mcd
			E3	10	-	-	
			E4	14	-	-	
			E5	48	-	-	